

AMENDMENTS TO THE CLAIMS:

Please amend claims 1, 3 and 4, as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (Currently amended): A monocrystalline gallium nitride localized substrate, comprising:

a monocrystalline silicon substrate;
a region of silicon carbide formed ~~on~~ by locally metamorphosing the monocrystalline silicon substrate into silicon carbide; and
a region of monocrystalline gallium nitride grown on the region of silicon carbide.

Claim 2 (canceled)

Claim 3 (Currently amended): A monocrystalline gallium nitride localized substrate according to claim 1, further comprising:

a region of silicon nitride formed on the monocrystalline silicon substrate ~~alongside of the region of silicon carbide,~~ the region of silicon nitride positioned other than in said region of monocrystalline gallium nitride.

Claim 4 (Currently amended): A monocrystalline gallium nitride localized substrate according to claim 1, further comprising:

a region of silicon oxide formed on the monocrystalline silicon substrate ~~alongside of the region of silicon carbide,~~ the region of silicon oxide positioned other than in said region of monocrystalline gallium nitride.

Claim 5 (Previously presented): A monocrystalline gallium nitride localized substrate according to Claim 1, wherein said monocrystalline silicon substrate is an SOI substrate.

Claims 6-9 (Canceled).

Claim 10 (Previously presented): A monocrystalline gallium nitride localized substrate according to Claim 3, wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 11 (Previously presented): A monocrystalline gallium nitride localized substrate according to Claim 4, wherein said monocrystalline silicon substrate is an SOI substrate.

Claim 12 (Previously presented): A monocrystalline gallium nitride localized substrate according to claim 3, further comprising:

a region of polycrystalline gallium nitride grown on the region of silicon nitride.

Claim 13 (Previously presented): A monocrystalline gallium nitride localized substrate according to claim 4, further comprising:

a region of polycrystalline gallium nitride grown on the region of silicon oxide.